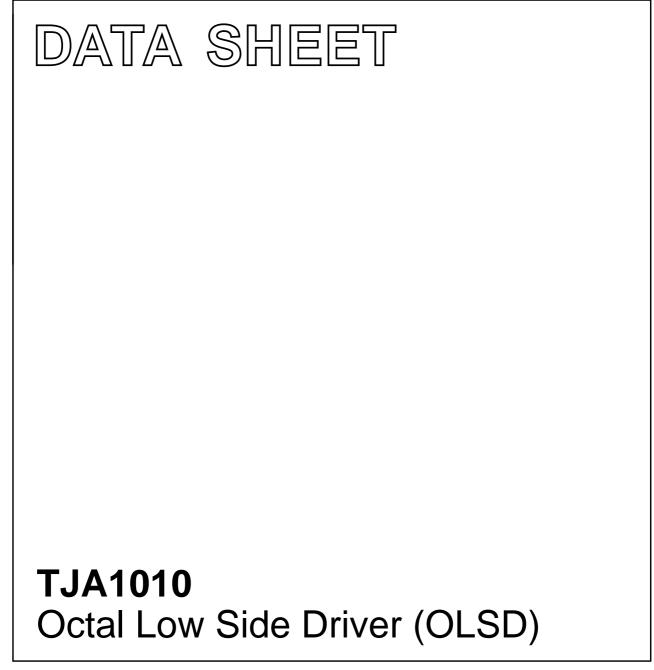
INTEGRATED CIRCUITS



Preliminary specification File under Integrated Circuits, IC18 1998 Feb 09



HILIP

TJA1010

FEATURES

- Eight independent low side drivers
- Small outline/medium power package for surface mounting, SO28 (20 + 4 + 4)
- · Serial input control by writing to internal shift register
- Overvoltage clamping for each driver
- Each driver protected against short-circuited load
- Undervoltage shutdown
- All logic pins CMOS microcontroller compatible
- Standby mode for minimum current consumption
- Two status outputs indicating short-circuited load and open load respectively at any driver stage
- Channel selective diagnostic information available by reading from internal shift register
- · Serial output allows cascading of several OLSDs
- Outputs can be used in parallel
- Two-stage thermal protection
- Power-on reset.

QUICK REFERENCE DATA

GENERAL DESCRIPTION

The TJA1010 is an octal low side driver for relays in automotive applications.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{DD}	supply voltage	operating	5.5	_	25	V
		load dump	-	-	50	V
V _{o(clamp)}	drain-to-source clamp voltage	l _o = 20 mA	50	60	70	V
R _{o(on)}	on resistance	I _o = 0.2 A	—	-	3	Ω
I _o	output current	continuous at all outputs; T _{amb} = 85 °C	-	-	0.2	A

ORDERING INFORMATION

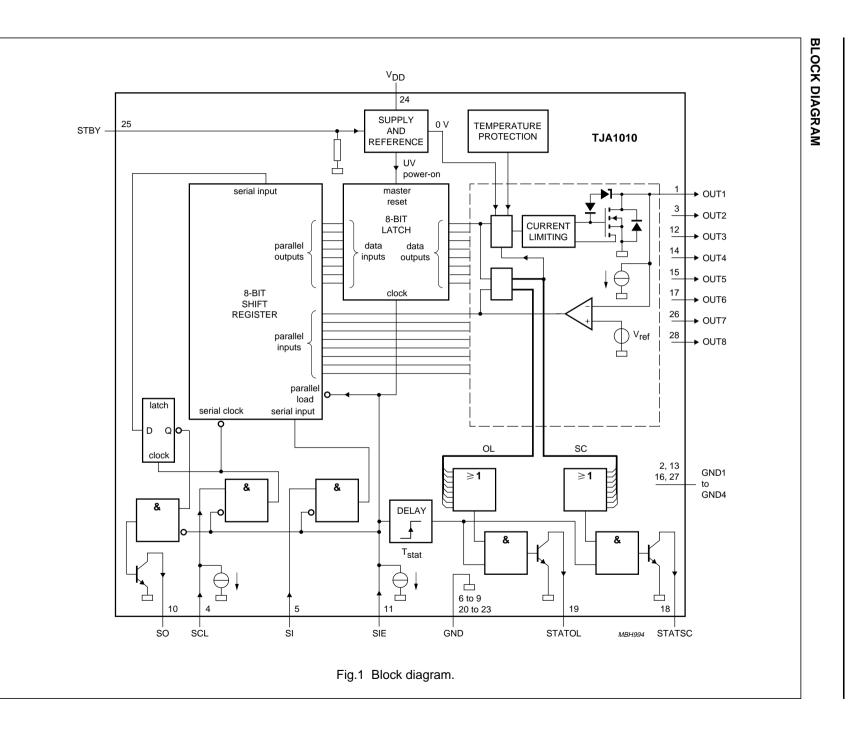
ТҮРЕ	PACKAGE			
NUMBER	NAME DESCRIPTION VERSIO			
TJA1010T	SO28	plastic small outline package; 28 leads; body width 7.5 mm	SOT136-1	



Preliminary specification

Octal Low Side Driver (OLSD)

TJA1010



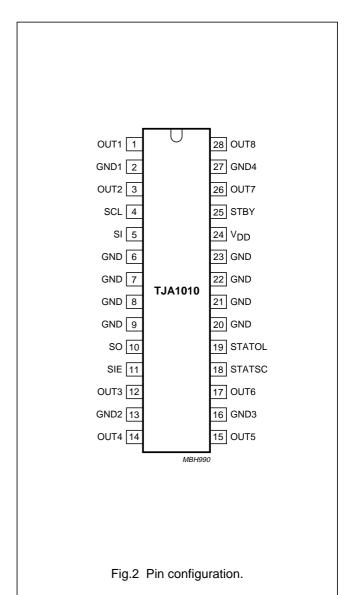
1998 Feb 09

_

ω

PINNING

SYMBOL	PIN	DESCRIPTION
OUT1	1	output 1
GND1	2	ground 1
OUT2	3	output 2
SCL	4	serial clock input
SI	5	serial input
GND	6	ground
GND	7	ground
GND	8	ground
GND	9	ground
SO	10	serial output
SIE	11	serial input enable
OUT3	12	output 3
GND2	13	ground 2
OUT4	14	output 4
OUT5	15	output 5
GND3	16	ground 3
OUT6	17	output 6
STATSC	18	status output short-circuited load
STATOL	19	status output open load
GND	20	ground
GND	21	ground
GND	22	ground
GND	23	ground
V _{DD}	24	supply voltage
STBY	25	standby input
OUT7	26	output 7
GND4	27	ground 4
OUT8	28	output 8



FUNCTIONAL DESCRIPTION (see Figs 1, 3 and 4)

This octal low side driver is intended to drive relays in automotive applications. It is optimized to withstand the wide temperature and supply voltage range that is typical for this application area. It consists of 8 protected outputs, including diagnostic functions, controlled by a serial interface. These outputs can be used in parallel without the need for additional components.

Serial control interface

Serial control of the drivers is provided by an 8-bit shift register with parallel outputs and an 8-bit latch which controls the DMOS output stages. Using this configuration the number of pins needed for control of the eight drivers is reduced to three; Serial Input (SI), Serial CLock (SCL) and Serial Input Enable (SIE). When pin SIE is LOW, serial data at pin SI is shifted into the shift register at each HIGH-to-LOW transition at the SCL pin and serial data is shifted out at the Serial Output (SO) pin at a LOW-to-HIGH transition on the SCL pin. The last bit read in before a LOW-to-HIGH transition at the SIE pin is bit D8. A HIGH level at the SI pin causes a driver to switch-on. With a LOW-to-HIGH transition at the SIE pin, parallel output data in the shift register is written to the 8-bit latch, which controls the DMOS outputs. When SIE is HIGH, signals at pins SI, SCL and SO are disabled. For pin SO this results in a HIGH level because pin SO is an open-collector output.

Diagnostic interface

The OLSD detects open loads and short-circuited loads at each driver stage by comparing its output voltages (V_o) to a reference voltage (V_{ref}). To allow distinction between short-circuit and open load conditions, a short-circuit is detected for V_o > V_{ref} in the on-state, while an open load is detected for V_o < V_{ref} in the off-state of a driver stage. In both cases the corresponding status pin is set to a LOW level and the respective bit in the shift register is inverted on a HIGH-to-LOW transition of SIE.

By writing a following byte into the shift register, its actual contents (the control byte eventually modified by errors) can be read out via pin SO. Comparing this byte with the original control byte previously written, faults can be localized and identified (e.g. open load at driver stage number 5).

Protection of DMOS outputs

Each driver contains a DMOS power FET. The drivers are protected against overvoltage, short-circuit and overtemperature conditions.

An overvoltage clamp circuit at each driver causes the respective DMOS power FET to turn partially on, if its drain-to-source voltage level exceeds the clamp level $[V_{o(clamp)}]$. Consequently each driver can withstand voltage peaks caused by turning off inductive loads, such as relays coils without freewheel diodes. It should be noted that if outputs are used in parallel the amount of inductive energy which can be handled will not increase but will remain equal to that of a single output.

Each driver is protected against a short-circuited load by current limiting. In the event of a short-circuited load at a driver stage, the current will be limited and the HIGH level of its drain-to-source voltage will force the comparator output to go HIGH. This in turn will set the STATSC pin to a LOW level.

A two-stage temperature protection circuit is included to protect the device against overheating caused by high dissipation in the output transistors.

When the temperature exceeds the overtemperature threshold level, it will switch-off those outputs with a short-circuit condition for the duration of the overtemperature condition. The status and diagnostic function will not be influenced.

If the chip temperature still rises and exceeds the emergency threshold level, the emergency shutdown will become active and shut down all of the outputs until the temperature drops below the overtemperature threshold.

The outputs are fully protected against short-circuit to battery conditions for the whole supply voltage range.

To protect the outputs against device threatening dissipation peaks, the overtemperature control is extended with local power dissipation sensors. If one or more outputs dissipate too much power all outputs with a short-circuit condition will be switched off for the duration of the local overtemperature condition.

To protect the outputs against high dissipation during load dump, an overvoltage protection is included. This will switch-off those outputs with a short-circuit condition if the supply voltage exceeds the overvoltage threshold $V_{DD(0 \ V)}$ for the duration of the overvoltage condition.

The diagnostic and status information will not change due to the interference of the overvoltage and overtemperature protections.

To avoid a false LOW signal at the SC pin due to switching transients at the DMOS outputs, the SC pin is disabled for a sufficient delay time whenever a new input control byte has been written into the 8-bit latch with a LOW-to-HIGH transition of SIE.

TJA1010

Other features

When using several OLSDs, input control and diagnostics can be provided, as described above, without spending further microcontroller pins by cascading, i.e. connecting the SO pin of one OLSD to the SI pin of the following OLSD.

A standby input (STBY) pin allows the off state current consumption in the OLSD to be minimized. Thus the OLSD can be connected permanently to a battery. A power-on reset ensures a defined off state for all drivers when the device is switched on i.e. by switching on the power supply or by activating the device via the STBY pin. Thus the STBY input can also be used as a reset pin.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{DD}	supply voltage	continuous	0	25	V
		transient	0	50	V
V _n	input voltage at pins SI, SCL and SIE		0	5.5	V
V _{I(STBY)}	input voltage at pin STBY		0	7	V
V _{o(STAT})	output voltage at pins STATOL and STATSC		0	18	V
V _{o(SO)}	output voltage at pin SO		0	18	V
lo	output current		internally	limited	•
I _{o(con)}	continuous output current	T _j = 135 °C	-0.2	+0.2	A
		T _j = 95 °C	-0.3	+0.3	A
I _{clamp(rep)}	repetitive inductive turn-off current per output	T _j = 135 °C; note 1	see Fig.5	see Fig.5 A	
E _{clamp(rep)}	repetitive inductive turn-off energy per output	T _j = 95 °C; notes 1 and 2	-	5	mJ
E _{clamp(nrep)}	non-repetitive inductive turn-off energy per output	$T_j = 95 \text{ °C}; \text{ notes 1 and 3}$	-	60	mJ
T _{vj}	virtual junction temperature		-40	+135	°C
T _{stg}	storage temperature		-55	+150	°C
V _{esd}	electrostatic handling	human body model	-	3	kV
		machine model	_	300	V

Notes

1. The amount of E_{clamp} per output can **NOT** be added if outputs are used in parallel. Thus, if two or more outputs are used in parallel it can handle the E_{clamp} of one output.

2. Defined for $t_{clamp} = 1$ ms.

3. Defined for $t_{clamp} = 5$ ms.

TJA1010

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th (j-amb)}	from junction to ambient in free air	note 1	55	K/W
R _{th (j-sp)}	from junction to soldering point of ground pins 6 to 9 and 20 to 23	note 2	17	K/W

Notes

- 1. Printed on an FR-4 board with minimum foot print.
- 2. Power uniformly divided over all outputs.

CHARACTERISTICS

 $T_j = -40$ to +135 °C; $V_{DD} = 11$ to 13.5 V; $V_{bat(max)} = V_{DD} + 1.5$ V. All voltages are defined with respect to ground. Positive currents flow into the IC. All parameters are guaranteed over the temperature range by design, but only 100% tested at $T_{amb} = 25$ °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{DD}	supply current	$I_0 = 0 \text{ mA}; V_{\text{STBY}} > 3 \text{ V}$	-	-	5	mA
		V _{STBY} < 1 V; V _{DD} = 13 V; T _j = -40 to +85 °C	-	-	10	μA
V _{DD(UV)}	undervoltage shutdown threshold		2	-	4.3	V
V _{DD(0V)}	overvoltage protection threshold		25	-	33	V
V _{o(clamp)}	output clamp voltage	l _o = 20 mA	50	60	70	V
I _{LO}	output leakage current	off-state, V _o = 13 V; standby	-		10	μA
	(one output)	off-state, V _o = 13 V; operational	70	-	210	μA
		off-state, V _o = 1 V; operational	40	_	180	μA
I _{o(lim)}	output current limit (one output)	on-state	0.3	_	0.55	А
R _o	output resistance (one output)	$I_o = 0.2 \text{ A}; V_{DD} = 13 \text{ V};$ $T_j = 135 \text{ °C}$	-	-	3	Ω
		$I_o = 0.2 \text{ A}; V_{DD} = 13 \text{ V};$ $T_j = 25^{\circ}\text{C}$	-	_	2.5	Ω
		I _o = 0.1 A; V _{DD} = 5.5 V; see Fig.6	-	-	10	Ω
V _{ref}	open load/short-circuit reference voltage	note 1	1	_	1.9	V
δl _o /δt	maximum rise and fall time of output current	$V_{DD} = 13 \text{ V}; \text{ R}_{L} = 100 \Omega;$ note 2	-	_	100	mA/μs
V _{IH}	HIGH-level input voltage at pins SI, SCL, SIE and STBY		3	_	-	V
V _{i(hys)}	input voltage hysteresis at pins SI, SCL and SIE	note 2	0.2	_	1.2	V
V _{IL}	LOW-level input voltage at pins SI, SCL and SIE		-	_	0.8	V
V _{IL(STBY)}	LOW-level input voltage at pin STBY		-	-	1	V

TJA1010

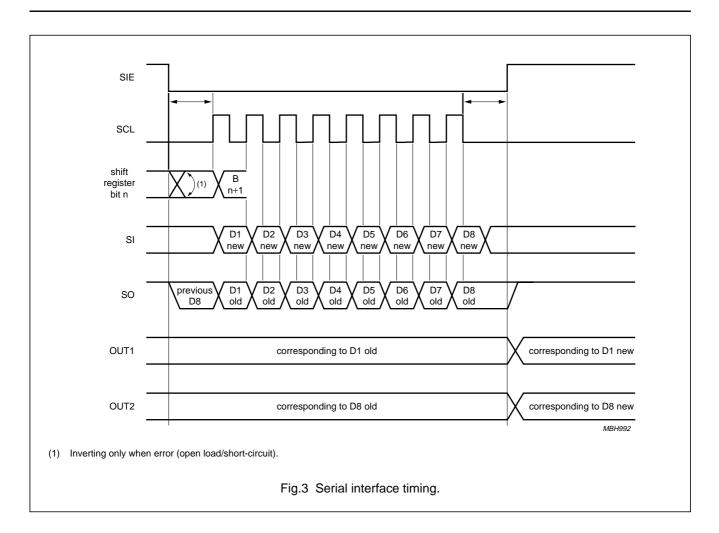
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
li	input current at pins SCL and SIE	V _i = 3 V	20	_	60	μA
ILI	input leakage current at pins SI, SIE and SCI	off-state; V _i = 3 V; T _j = 85 °C; V _{STBY} < 1 V	-	-	5	μA
R _{i(STBY)}	input resistance at pin STBY	V _i = 1 V; T _j < 85 °C	40	-	150	kΩ
I _{i(STBY)}	input current at pin STBY	V _i = 3 V	20	-	60	μA
V _{STAT(L)}	status LOW voltage	I _{STAT(L)} = 1.6 mA	-	-	0.4	V
V _{SO(L)}	serial output LOW voltage	I _{SO} = 1.6 mA	-	_	0.4	V
I _{LO(SO)}	output leakage current at pin SO and status outputs	off-state; V _o = 5 V; V _{STBY} < 1 V; T _j < 85 °C	-	-	10	μA
f _{clk}	clock frequency		-	-	1	MHz
t _{W(SCL)}	SCL positive pulse width	HIGH-to-LOW transition	500	-	-	ns
$t_{d(SIE-SCL)}$	delay time from SIE HIGH to SCL LOW		100	-	-	ns
$t_{su(SIE-SCL)}$	set-up time from SIE LOW to SCL HIGH		250	-	-	ns
t _{d(SCL-SO)}	delay time from SCL HIGH to SO valid	note 3	-	-	250	ns
t _{su(SI-SCL)}	set-up time from SI to falling edge of SCL		150	-	-	ns
t _{h(SCL-SI)}	hold time from falling edge of SCL to SI		150	-	-	ns
t _{h(SCL-SIE)}	hold time from SCL LOW to SIE HIGH		250	-	-	ns
t _{su(STBY)}	STBY set-up time from STBY HIGH to SIE LOW		100	-	-	μs
t _{h(STBY)}	STBY hold time from SIE HIGH to STBY LOW		10	-	-	μs
t _{d(STAT)}	delay time for status pin enable		40	100	250	μs
T _{th(otc)}	threshold overtemperature control		-	170	-	°C
T _{th(ets)}	threshold emergency temperature shutdown		-	190	-	°C

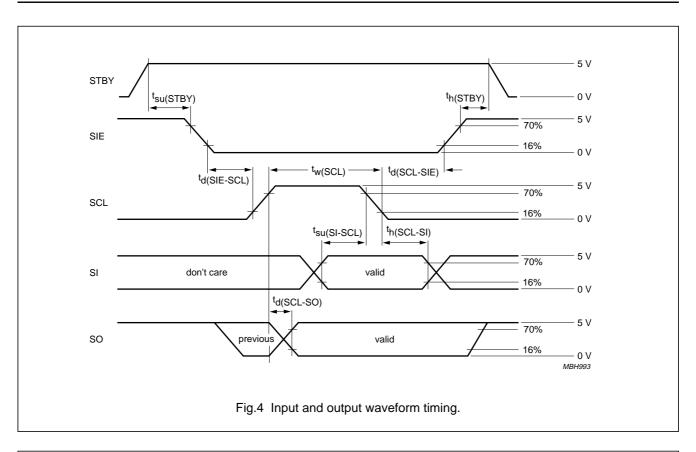
Notes

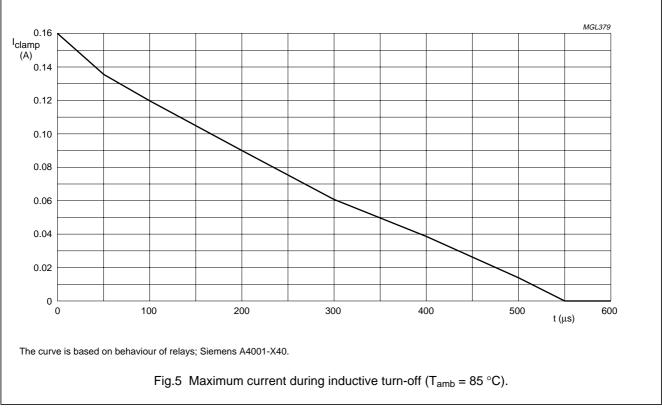
1. Open load is indicated for $V_o < V_{ref}$ in the off-state, short-circuited load is indicated for $V_o > V_{ref}$ in the on-state.

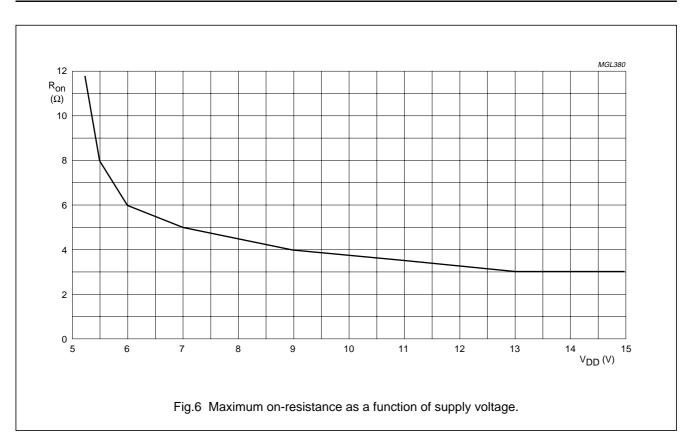
2. Guaranteed by design.

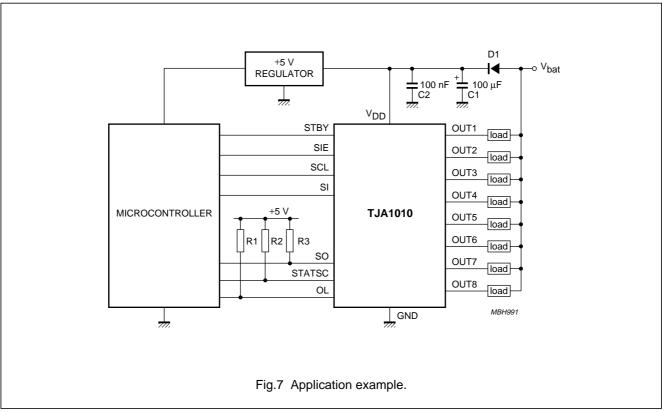
3. Delay caused by load excluded.





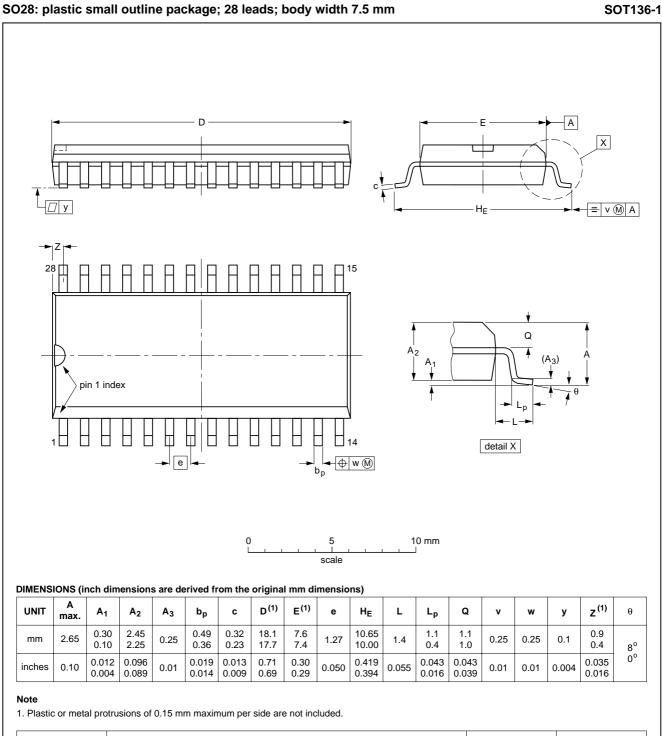






TJA1010

PACKAGE OUTLINE



OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT136-1	075E06	MS-013AE			-95-01-24 97-05-22	

TJA1010

SOLDERING

Introduction

There is no soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and surface mounted components are mixed on one printed-circuit board. However, wave soldering is not always suitable for surface mounted ICs, or for printed-circuits with high population densities. In these situations reflow soldering is often used.

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"IC Package Databook"* (order code 9398 652 90011).

Reflow soldering

Reflow soldering techniques are suitable for all SO packages.

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several techniques exist for reflowing; for example, thermal conduction by heated belt. Dwell times vary between 50 and 300 seconds depending on heating method. Typical reflow temperatures range from 215 to 250 °C.

Preheating is necessary to dry the paste and evaporate the binding agent. Preheating duration: 45 minutes at 45 °C.

Wave soldering

Wave soldering techniques can be used for all SO packages if the following conditions are observed:

- A double-wave (a turbulent wave with high upward pressure followed by a smooth laminar wave) soldering technique should be used.
- The longitudinal axis of the package footprint must be parallel to the solder flow.
- The package footprint must incorporate solder thieves at the downstream end.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder is 10 seconds, if cooled to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Repairing soldered joints

Fix the component by first soldering two diagonallyopposite end leads. Use only a low voltage soldering iron (less than 24 V) applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C. When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

TJA1010

DEFINITIONS

Data sheet status					
Objective specification	ation This data sheet contains target or goal specifications for product development.				
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.				
Product specification	This data sheet contains final product specifications.				
Limiting values					
more of the limiting values r of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or nay cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification imiting values for extended periods may affect device reliability.				
Application information					
Where application information is given, it is advisory and does not form part of the specification.					

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

TJA1010

NOTES

Philips Semiconductors – a worldwide company

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB, Argentina: see South America Tel. +31 40 27 82785, Fax. +31 40 27 88399 Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113, New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +61 2 9805 4455, Fax. +61 2 9805 4466 Tel. +64 9 849 4160, Fax. +64 9 849 7811 Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010, Norway: Box 1, Manglerud 0612, OSLO, Fax. +43 160 101 1210 Tel. +47 22 74 8000, Fax. +47 22 74 8341 Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773 Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Belgium: see The Netherlands Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474 Brazil: see South America Poland: UI. Lukiska 10, PL 04-123 WARSZAWA, Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor, Tel. +48 22 612 2831, Fax. +48 22 612 2327 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102 Portugal: see Spain Romania: see Italy Canada: PHILIPS SEMICONDUCTORS/COMPONENTS, Tel. +1 800 234 7381 Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW, Tel. +7 095 755 6918, Fax. +7 095 755 6919 China/Hong Kong: 501 Hong Kong Industrial Technology Centre, 72 Tat Chee Avenue, Kowloon Tong, HONG KONG, Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231, Tel. +852 2319 7888, Fax. +852 2319 7700 Tel. +65 350 2538, Fax. +65 251 6500 Slovakia: see Austria Colombia: see South America Czech Republic: see Austria Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S, Tel. +45 32 88 2636, Fax. +45 31 57 0044 Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920 France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex, Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427 Germany: Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +49 40 23 53 60, Fax. +49 40 23 536 300 Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS, Tel. +30 1 4894 339/239, Fax. +30 1 4814 240 Hungary: see Austria India: Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025, Tel. +91 22 493 8541, Fax. +91 22 493 0966 Indonesia: see Singapore Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000, Fax. +353 1 7640 200 Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007 Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557 Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108, Tel. +81 3 3740 5130, Fax. +81 3 3740 5077 Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +82 2 709 1412, Fax. +82 2 709 1415 Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Tel. +60 3 750 5214, Fax. +60 3 757 4880 Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,

Tel. +9-5 800 234 7381 Middle East: see Italy

For all other countries apply to: Philips Semiconductors, International Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

© Philips Electronics N.V. 1998

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

615102/00/01/pp16

Document order number: 9397 750 01763

SCA57

Let's make things better.







Internet: http://www.semiconductors.philips.com

Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale, 2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000, Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Al. Vicente Pinzon, 173, 6th floor, 04547-130 SÃO PAULO, SP, Brazil,

Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22 08007 BARCELONA Tel. +34 3 301 6312, Fax. +34 3 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM, Tel. +46 8 632 2000, Fax. +46 8 632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH, Tel. +41 1 488 2686, Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1, TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd. 209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260, Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL, Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7, 252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Haves. MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409, Tel. +1 800 234 7381

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD, Tel. +381 11 625 344, Fax.+381 11 635 777

Date of release: 1998 Feb 09